IN THE CLAIMS:

Please cancel claim 4; amend claims 1, 5, 7, and 9; and add new claims 21-34, as follows:

1. (Currently amended) A semiconductor device, wherein a semiconductor substrate has a semiconductor element which is formed in a major surface, the semiconductor substrate has a thickness between 20-60 μm, and at least some of edges where side surfaces of the semiconductor substrate and a backside surface of the major surface cross comprise curved surfaces having a radius of curvature of 0.5 to 50 μm.

2. (Original) The device according to claim 1, wherein the curved surfaces are formed at all portions where the side surfaces and the backside surface of the semiconductor substrate cross.

3. (Original) The device according to claim 1, wherein the semiconductor substrate has a rectangular shape, and the curved surfaces are formed at edges corresponding to long sides of the semiconductor substrates.

4. (Canceled)

5. (Currently amended) The device according to claim [[4]] 1, wherein the semiconductor substrate preferably has a thickness of 20 to 40μm.

6. (Original) The device according to claim 1, which further comprises bonding pads formed on the major surface side of the semiconductor substrate, and in which the curved surfaces are formed in regions outside the bonding pads.

7. (Currently amended) ~~The device according to claim 1, which~~ A semiconductor device, wherein a semiconductor substrate has a semiconductor element which is formed in a

major surface and at least some of edges where side surfaces of the semiconductor substrate and a backside surface of the major surface cross comprise curved surfaces having a radius of curvature of 0.5 to 50 μm, wherein the device further comprises a guard ring formed on the major surface side of the semiconductor substrate, and in which the curved surfaces are formed in regions outside the guard ring.

8. (Original) The device according to claim 1, wherein the curved surfaces have no inflection points.

9. (Currently amended) ~~The device according to claim 1, wherein~~ A semiconductor device, wherein a semiconductor substrate has a semiconductor element which is formed in a major surface and at least some of edges where side surfaces of the semiconductor substrate and a backside surface of the major surface cross comprising curved surfaces having a radius of curvature of 0.5 to 50 μm, and wherein the backside surface of the semiconductor substrate is a mirror surface.

10. (Canceled)

11. (Canceled)

12. (Canceled)

13. (Canceled)

14. (Canceled)

15. (Canceled)

16. (Canceled)

17. (Canceled)

18. (Canceled)

19. (Canceled)

20. (Canceled)

21. (New) The device according to claim 7, wherein the curved surfaces are formed at all portions where the side surfaces and the backside surface of the semiconductor substrate cross.

22. (New) The device according to claim 7, wherein the semiconductor substrate has a rectangular shape, and the curved surfaces are formed at edges corresponding to long sides of the semiconductor substrates.

23. (New) The device according to claim 7, wherein the semiconductor substrate has a thickness of 20 to 60 μm.

24. (New) The device according to claim 23, wherein the semiconductor substrate preferably has a thickness of 20 to 40 μm.

25. (New) The device according to claim 7, which further comprises bonding pads formed on the major surface side of the semiconductor substrate, and in which the curved surfaces are formed in regions outside the bonding pads.

26. (New) The device according to claim 7, wherein the curved surfaces have no inflection points.

27. (New) The device according to claim 7, wherein the backside surface of the semiconductor substrate is a mirror surface.

28. (New) The device according to claim 9, wherein the curved surfaces are formed at all portions where the side surfaces and the backside surface of the semiconductor substrate cross.

29. (New) The device according to claim 9, wherein the semiconductor substrate has a rectangular shape, and the curved surfaces are formed at edges corresponding to long sides of the semiconductor substrates.

30. (New) The device according to claim 9, wherein the semiconductor substrate has a thickness of 20 to 60 μm.

31. (New) The device according to claim 30, wherein the semiconductor substrate preferably has a thickness of 20 to 40 μm.

32. (New) The device according to claim 9, which further comprises bonding pads formed on the major surface side of the semiconductor substrate, and in which the curved surfaces are formed in regions outside the bonding pads.

33. (New) The device according to claim 9, which further comprises a guard ring formed on the major surface side of the semiconductor substrate, and in which the curved surfaces are formed in regions outside the guard ring.

34. (New) The device according to claim 9, wherein the curved surfaces have no inflection points.